XM3400 N-Channel Enhancement Mode Power MOSFET

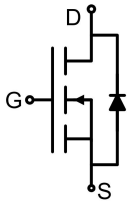
Description

The XM3400 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

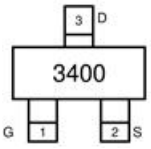
General Features

- V_{DS} = 30V, I_D = 5.5A
  $R_{DS(ON)}$ < 57mΩ @ V_{GS}=2.5V
  $R_{DS(ON)}$ < 41mΩ @ V_{GS}=4.5V
  $R_{DS(ON)}$ < 35mΩ @ V_{GS}=10V
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin assignment



SOT-23 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Quantity
3400	XM3400	SOT-23	3000 units

Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current-Continuous	I_D	5.5	A
Drain Current-Pulsed (Note 1)	I_{DM}	30	A
Maximum Power Dissipation	P_D	1.4	W
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	89	℃/W

@Copyright Sunravell Semiconductor Inc. All Rights Reserved.

Electrical Characteristics (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	30	33	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±12V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	0.7	0.9	1.2	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=2.5V, I_D=4A	-	28	57	mΩ
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=4.5V, I_D=5A	-	18	41	mΩ
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=5A	-	15	35	mΩ
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=5A	10	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{iss}	V_{DS}=15V,V_{GS}=0V,	-	820	-	PF
Output Capacitance	C_{oss}	F=1.0MHz	-	99	-	PF
Reverse Transfer Capacitance	C_{rss}		-	77	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=15V, R_L=2.7Ω	-	3.3	-	nS
Turn-on Rise Time	t_r	V_{GS}=10V, R_G=3Ω	-	4.8	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	26	-	nS
Turn-Off Fall Time	t_f		-	4	-	nS
Total Gate Charge	Q_g	V_{DS}=15V,I_D=5A,	-	9.5	-	nC
Gate-Source Charge	Q_{gs}	V_{GS}=4.5V	-	1.5	-	nC
Gate-Drain Charge	Q_{gd}		-	3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=5A	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	5.5	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

@Copyright Sunravell Semiconductor Inc. All Rights Reserved.

Typical Electrical and Thermal Characteristics

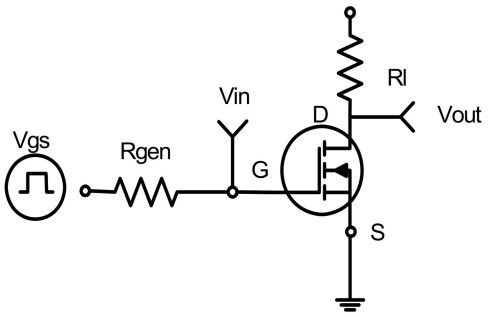


Figure 1:Switching Test Circuit

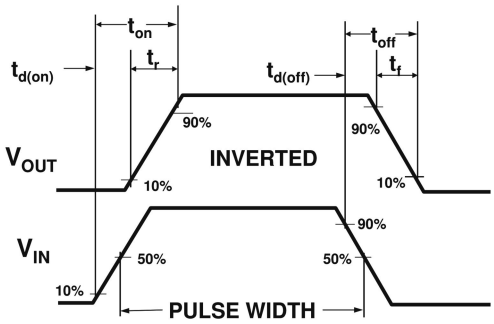


Figure 2:Switching Waveforms

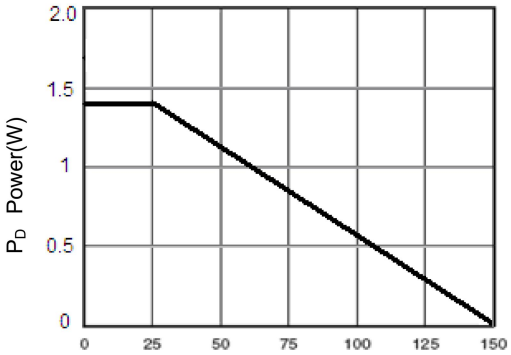


Figure 3 Power Dissipation

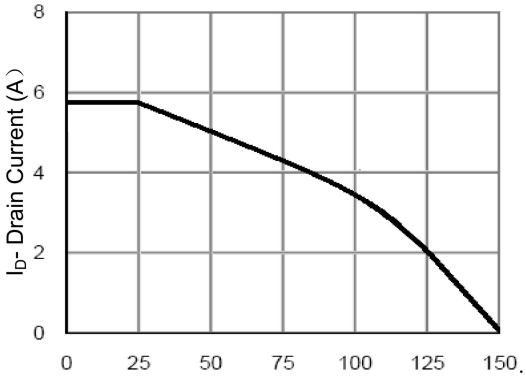


Figure 4 Drain Current

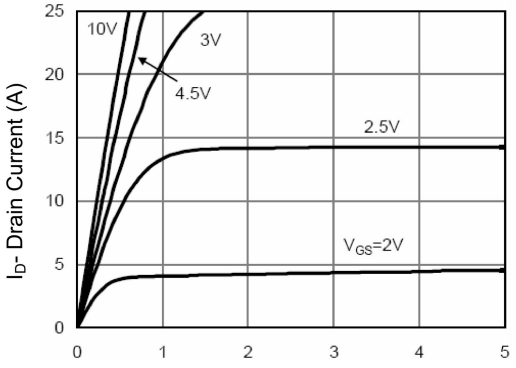


Figure 5 Output Characteristics

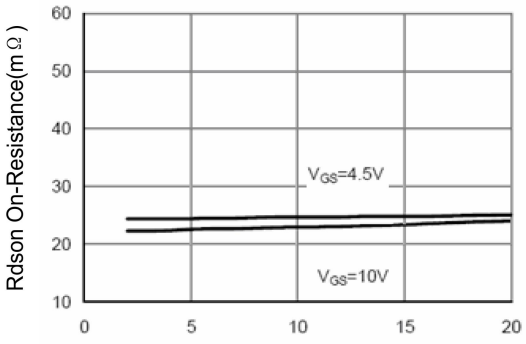


Figure 6 Drain-Source On-Resistance

@Copyright Sunravell Semiconductor Inc. All Rights Reserved.

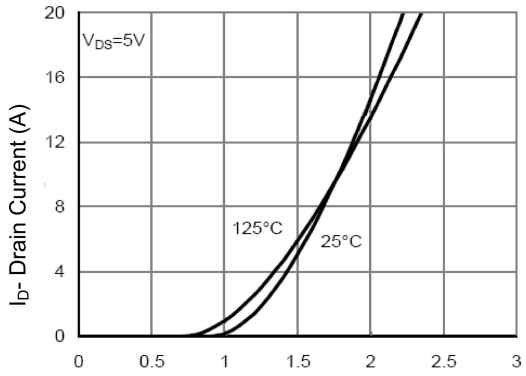


Figure 7 Transfer Characteristics

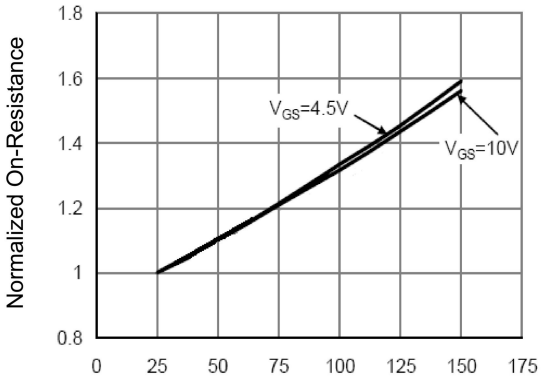


Figure 8 Drain-Source On-Resistance

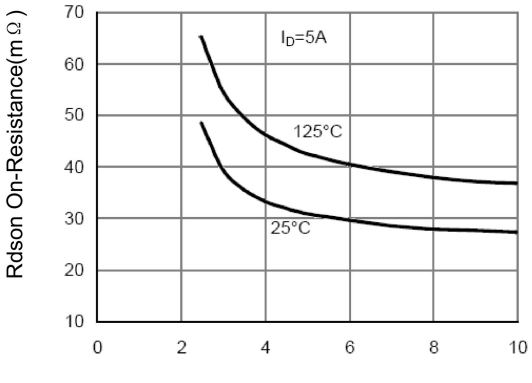


Figure 9 Rdson vs Vgs

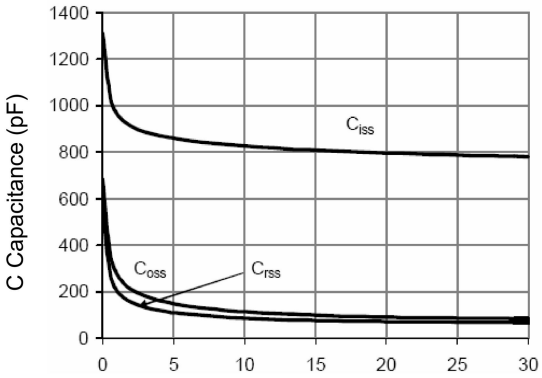


Figure 10 Capacitance vs Vds

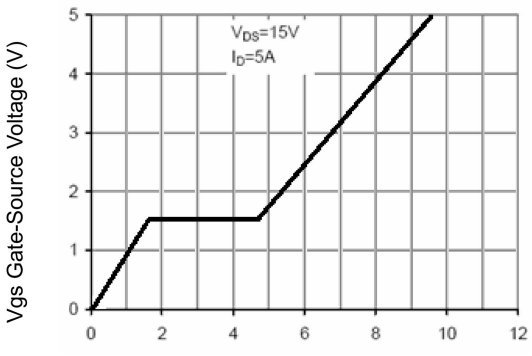


Figure 11 Gate Charge

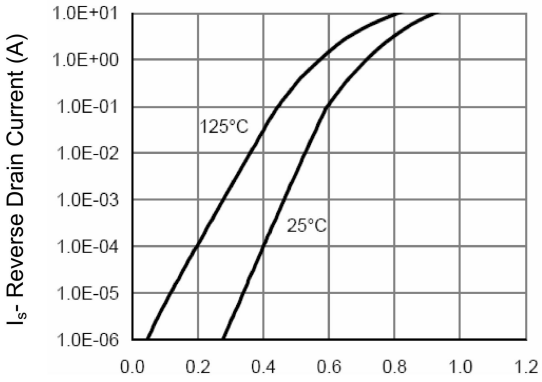
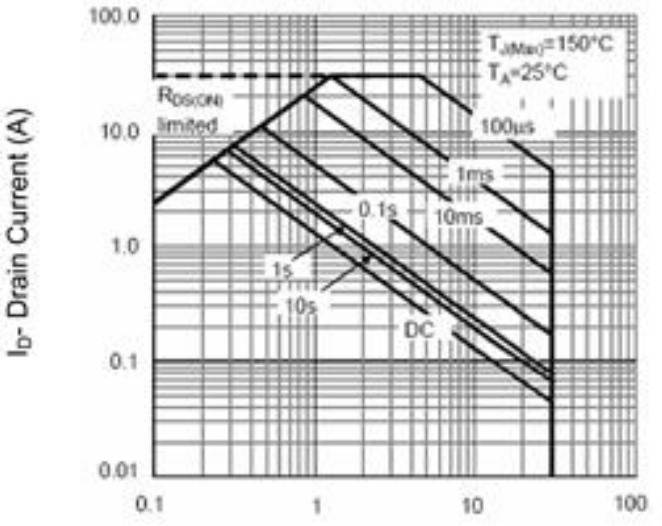


Figure 12 Source- Drain Diode Forward

@Copyright Sunravell Semiconductor Inc. All Rights Reserved.



Vds Drain-Source Voltage (V)

Figure 13 Safe Operation Area

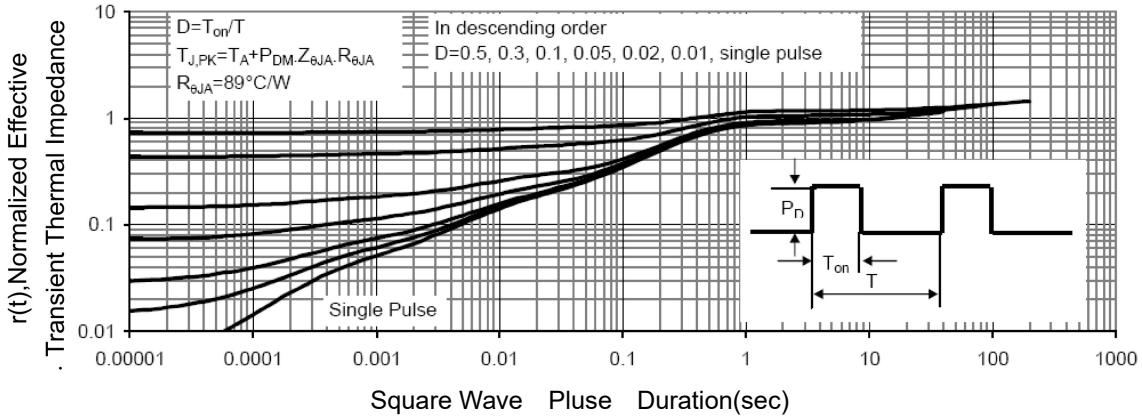
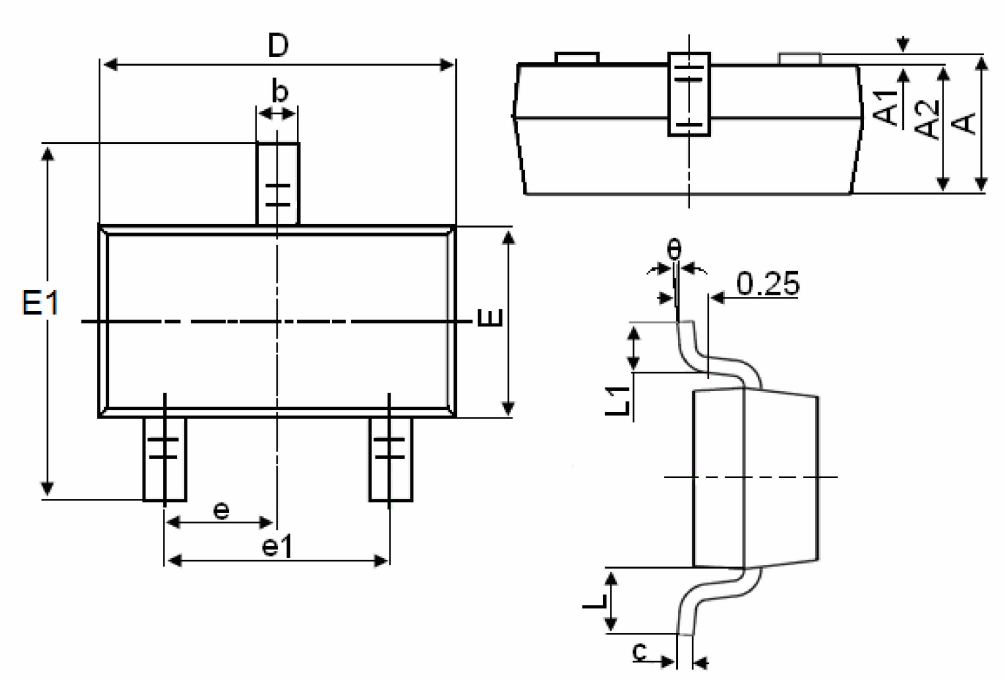


Figure 14 Normalized Maximum Transient Thermal Impedance

@Copyright Sunravell Semiconductor Inc. All Rights Reserved.

SOT-23 Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

Notes

1. All dimensions are in millimeters.
2. Tolerance ±0.10mm (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

@Copyright Sunravell Semiconductor Inc. All Rights Reserved.